

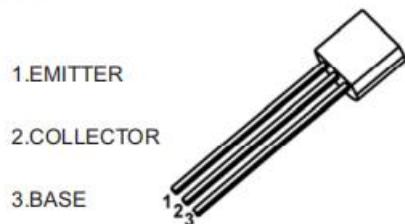
## TO-92 Bipolar Transistor 双极型三极管

TO - 92

### ■ Features 特点

### PNP General Purpose 通用

### ■ Absolute Maximum Ratings 最大额定值



Characteristic 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V <sub>CBO</sub>	-35	V
Collector-Emitter Voltage 集电极发射极电压	V <sub>CEO</sub>	-30	V
Emitter-Base Voltage 发射极基极电压	V <sub>EBO</sub>	-5	V
Collector Current 集电极电流	I <sub>C</sub>	-800	mA
Power dissipation 耗散功率	P <sub>C</sub> (T <sub>a</sub> =25°C)	625	mW
Thermal Resistance Junction-Ambient 热阻	R <sub>θJA</sub>	200	°C/W
Junction and Storage Temperature 结温和储藏温度	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150°C	

### ■ Device Marking 产品打标

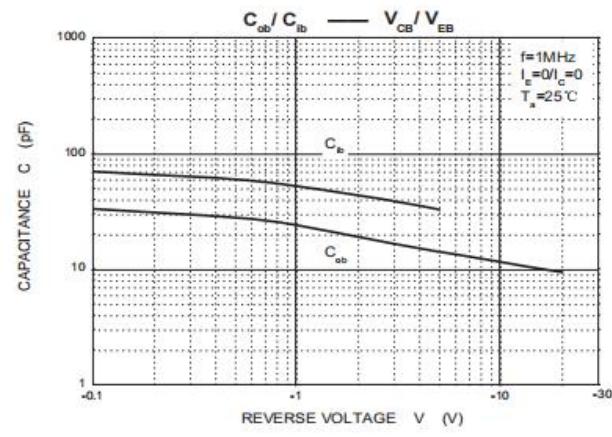
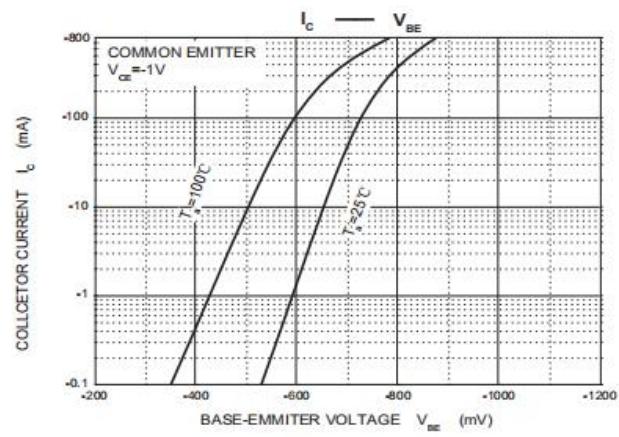
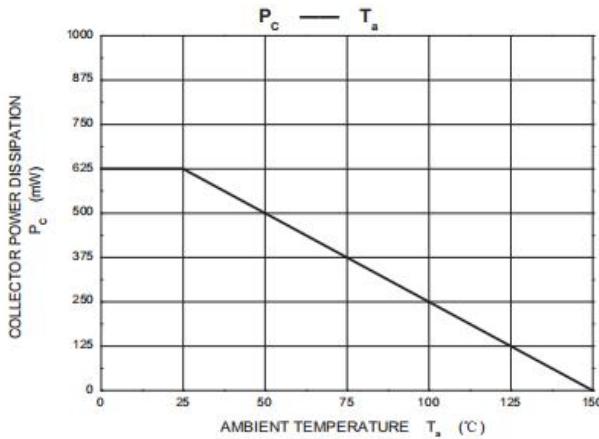
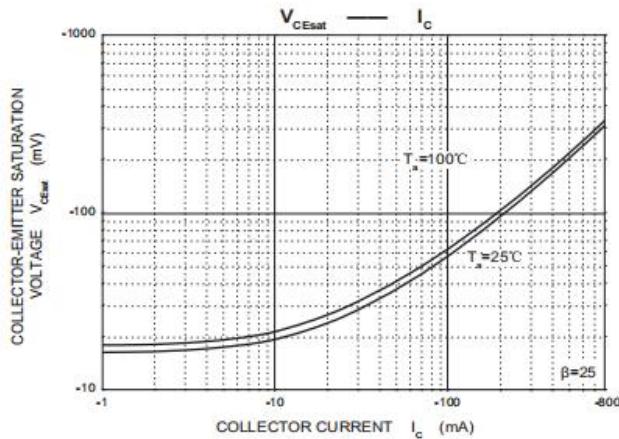
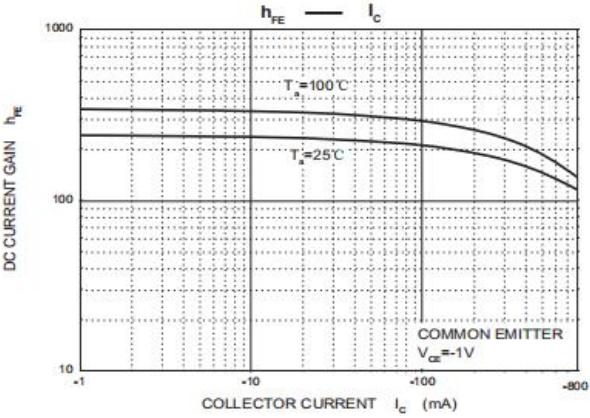
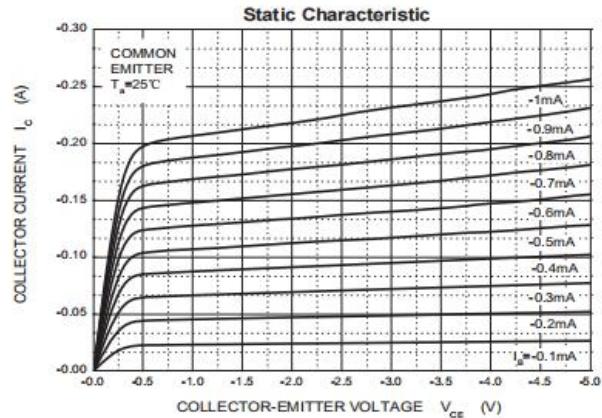
H <sub>FE</sub> (1)	100-200(O)	160-320(Y)
Mark	A1271	

## ■ Electrical Characteristics 电特性

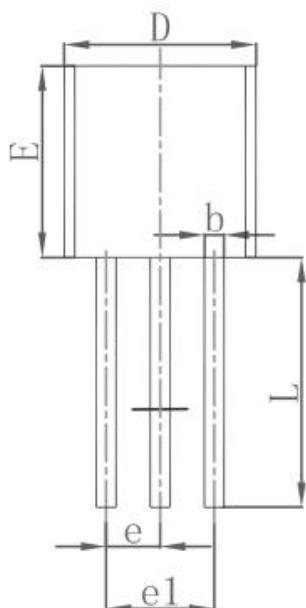
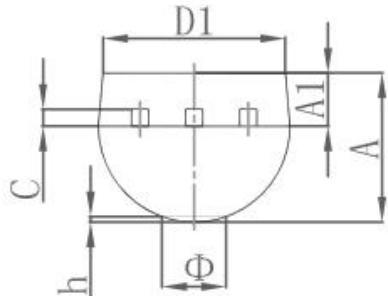
( $T_A=25^\circ\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^\circ\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压( $I_C = -100\mu\text{A}$ , $I_E = 0$ )	$\text{BV}_{\text{CBO}}$	-35	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压( $I_C = -10\text{mA}$ , $I_B = 0$ )	$\text{BV}_{\text{CEO}}$	-30	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压( $I_E = -100\mu\text{A}$ , $I_C = 0$ )	$\text{BV}_{\text{EBO}}$	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流( $V_{\text{CB}} = -35\text{V}$ , $I_E = 0$ )	$I_{\text{CBO}}$	—	—	-0.1	$\mu\text{A}$
Collector-Emitter Leakage Current 集电极发射漏电流( $V_{\text{CE}} = -25\text{V}$ , $I_E = 0$ )	$I_{\text{CBO}}$	—	—	-0.2	$\mu\text{A}$
Emitter-Base Leakage Current 发射极基极漏电流( $V_{\text{EB}} = -5\text{V}$ , $I_C = 0$ )	$I_{\text{EBO}}$	—	—	-0.1	$\mu\text{A}$
DC Current Gain 直流电流增益( $V_{\text{CE}} = -1\text{V}$ , $I_C = -100\text{mA}$ )	$H_{\text{FE}}(1)$	100	—	320	
DC Current Gain 直流电流增益( $V_{\text{CE}} = -1\text{V}$ , $I_C = -700\text{mA}$ )	$H_{\text{FE}}(2)$	35	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降( $I_C = -500\text{mA}$ , $I_B = -20\text{mA}$ )	$V_{\text{CE}(\text{sat})}$	—	—	-0.7	V
Base-Emitter On Voltage 基极发射极导通电压( $V_{\text{CE}} = -1\text{V}$ , $I_C = -10\text{mA}$ )	$V_{\text{BE}(\text{on})}$	—	—	-0.8	V
Output Capacitance 输出电容( $V_{\text{CB}} = -10\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$ )	$C_{\text{ob}}$	—	19	—	pF
Transition Frequency 特征频率( $V_{\text{CE}} = -5\text{V}$ , $I_C = -10\text{mA}$ )	$f_T$	—	120	—	MHz

## ■Typical Characteristic Curve 典型特性曲线



■ Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015